

# Sergey A Dvoretzkiy

## List of Publications by Year in descending order

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214  
papers

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147801

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49  
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216  
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docs citations

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times ranked

1325  
citing authors

#	ARTICLE	IF	CITATIONS
1	<p>&lt;mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"&gt;&lt;mml:mrow&gt;&lt;mml:mn&gt;4&lt;/mml:mn&gt;&lt;mml:mi&gt;I&lt;/mml:mi&gt;&lt;/mml:mrow&gt;&lt;/mml:math&gt;-periodic supercurrent tuned by an axial magnetic flux in topological insulator nanowires. Physical Review Research, 2022, 4, .</p>	3.6	13
2	Engineering topological phases in triple HgTe/CdTe quantum wells. Scientific Reports, 2022, 12, 2617.	3.3	3
3	Rashba Spin Splitting in HgCdTe Quantum Wells with Inverted and Normal Band Structures. Nanomaterials, 2022, 12, 1238.	4.1	2
4	Edge and Bulk Transport in a Two-Dimensional Topological Insulator Based on a CdHgTe Quantum Well. JETP Letters, 2022, 115, 202-207.	1.4	1
5	Terahertz Magnetospectroscopy of Cyclotron Resonances from Topological Surface States in Thick Films of Cd <sub>1-x</sub> Hg <sub>x</sub> Te. Physica Status Solidi (B): Basic Research, 2021, 258, 2000023.	1.5	8
6	Multiple crossings of Landau levels of two-dimensional fermions in double HgTe quantum wells. Physical Review B, 2021, 103, .	3.2	3
7	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. Technical Physics Letters, 2021, 47, 154-157.	0.7	1
8	Photothermal Ionization Spectroscopy of Mercury Vacancies in HgCdTe Epitaxial Films. JETP Letters, 2021, 113, 402-408.	1.4	3
9	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. Journal of Applied Physics, 2021, 129, .	2.5	11
10	Distinction between electron states formed at topological insulator interfaces with the trivial phase and vacuum. Scientific Reports, 2021, 11, 11638.	3.3	1
11	Optical Studies and Transmission Electron Microscopy of HgCdTe Quantum Well Heterostructures for Very Long Wavelength Lasers. Nanomaterials, 2021, 11, 1855.	4.1	6
12	THz polarization-dependent response of antenna-coupled HgCdTe photoconductors under an external constant electric field. Semiconductor Science and Technology, 2021, 36, 105009.	2.0	2
13	Non-local terahertz photoconductivity in the topological phase of Hg <sub>1-x</sub> Cd <sub>x</sub> Te. Scientific Reports, 2021, 11, 1587.	3.3	9
14	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. Laser Physics, 2021, 31, 015801.	1.2	7
15	Localization of helical edge states in the absence of external magnetic field. Physical Review B, 2021, 104, .	3.2	3
16	Coherent Emission in the Vicinity of 10 THz due to Auger-Suppressed Recombination of Dirac Fermions in HgCdTe Quantum Wells. ACS Photonics, 2021, 8, 3526-3535.	6.6	17
17	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at $\lambda \approx 4.6 \mu\text{m}$ wavelength from HgCdTe quantum wells. Journal of Applied Physics, 2021, 130, .	2.5	7
18	Generation of Terahertz Radiation in InP:Fe Crystals Due to Second-Order Lattice Nonlinearity. Semiconductors, 2021, 55, 785-789.	0.5	0

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19	Characterization of Crystal Perfection in the Layers of (013)HgCdTe/CdTe/ZnTe/GaAs Heterostructures via the Second Harmonic Generation Method. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2021, 57, 458-467.	0.6	0
20	Effect of Internal Optical Losses on the Generation of Mid-IR Stimulated Emission in Waveguide Heterostructures with HgCdTe/CdHgTe Quantum Wells. <i>Semiconductors</i> , 2021, 55, 899-902.	0.5	0
21	Preparation of Atomically Clean and Structurally Ordered Surfaces of Epitaxial CdTe Films for Subsequent Epitaxy. <i>Semiconductors</i> , 2021, 55, S62-S66.	0.5	5
22	TEM studies of structural defects in HgTe/HgCdTe quantum wells. <i>Applied Nanoscience (Switzerland)</i> , 2020, 10, 2867-2871.	3.1	4
23	Investigation of the Photosensitivity of Narrow-Gap and Gapless HgCdTe Solid Solutions in the Terahertz and Sub-Terahertz Range. <i>Semiconductors</i> , 2020, 54, 1096-1102.	0.5	1
24	Anisotropy of the in-plane g-factor of electrons in HgTe quantum wells. <i>Physical Review B</i> , 2020, 101, .	3.2	3
25	Unconventional reentrant quantum Hall effect in a HgTe/CdHgTe double quantum well. <i>Physical Review B</i> , 2020, 102, .	3.2	9
26	Effective Mass and g-Factor of Two-Dimensional HgTe $\Gamma_8$ -Band Electrons: Shubnikov-de Haas Oscillations. <i>Semiconductors</i> , 2020, 54, 982-990.	0.5	2
27	Quantum Hall states in inverted HgTe quantum wells probed by transconductance fluctuations. <i>Physical Review B</i> , 2020, 102, .	3.2	1
28	Many-particle effects in optical transitions from zero-mode Landau levels in HgTe quantum wells. <i>Physical Review B</i> , 2020, 102, .	3.2	3
29	Probing States of a Double Acceptor in CdHgTe Heterostructures via Optical Gating. <i>JETP Letters</i> , 2020, 111, 575-581.	1.4	5
30	Transport Features in the Topological Phase Hg <sub>0.87</sub> Cd <sub>0.13</sub> Te under Terahertz Photoexcitation. <i>Semiconductors</i> , 2020, 54, 1064-1068.	0.5	0
31	Continuous-Wave Stimulated Emission in the 10 $\mu$ m-14 $\mu$ m Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. <i>Semiconductors</i> , 2020, 54, 1371-1375.	0.5	2
32	Magnetic Susceptibility Measurements in HgTe Quantum Wells in a Perpendicular Magnetic Field. <i>JETP Letters</i> , 2020, 111, 633-638.	1.4	3
33	Magneto-intersubband oscillations in two-dimensional systems with an energy spectrum split due to spin-orbit interaction. <i>Physical Review B</i> , 2020, 101, .	3.2	10
34	Two-dimensional topological insulator state in double HgTe quantum well. <i>Physical Review B</i> , 2020, 101, .	3.2	13
35	Density of states measurements for the heavy subband of holes in HgTe quantum wells. <i>Physical Review B</i> , 2020, 101, .	3.2	3
36	Apparent PT-symmetric terahertz photoconductivity in the topological phase of Hg <sub>1-x</sub> CdxTe-based structures. <i>Scientific Reports</i> , 2020, 10, 2377.	3.3	12

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37	Possibilities of Characterizing the Crystal Parameters of Cd <sub>x</sub> Hg <sub>1-x</sub> Te Structures on GaAs Substrates by the Method of Generation of the Probe-Radiation Second Harmonic in Reflection Geometry. <i>Physics of the Solid State</i> , 2020, 62, 252-259.	0.6	5
38	HgCdTe-Based 640 Å– 512 Matrix Midwave Infrared Photodetector. <i>Journal of Communications Technology and Electronics</i> , 2020, 65, 316-320.	0.5	3
39	Impact Ionization Induced by Terahertz Radiation in HgTe Quantum Wells of Critical Thickness. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2020, 41, 1155-1169.	2.2	3
40	Symmetry breaking and circular photogalvanic effect in epitaxial <math>\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML">< mml:mrow>< mml:msub>< mml:mi>Cd</mml:mi>< mml:mi>_{24}</mml:mi>< mml:mi>_{11}</mml:mi></mml:math> films. <i>Physical Review Materials</i> , 2020, 4, .	2.4	11
41	Quantum Hall effect and Landau levels in the three-dimensional topological insulator HgTe. <i>Physical Review Research</i> , 2020, 2, .	3.6	12
42	Topological insulators based on HgTe. <i>Physics-Usppekhi</i> , 2020, 63, 629-647.	2.2	18
43	Investigation of Stimulated Emission from HgTe/CdHgTe Quantum-Well Heterostructures in the 3–5 $\mu$ m Atmospheric Transparency Window. <i>Semiconductors</i> , 2020, 54, 1365-1370.	0.5	0
44	Mid-infrared stimulated emission in HgCdTe/CdHgTe quantum well heterostructures at room temperature. <i>Optical Engineering</i> , 2020, 60, .	1.0	5
45	Urbach tail and nonuniformity probe of HgCdTe thin films and quantum well heterostructures grown by molecular beam epitaxy. <i>Optical Engineering</i> , 2020, 60, .	1.0	4
46	Effects of the Electron–Electron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. <i>JETP Letters</i> , 2020, 112, 508-512.	1.4	1
47	Molecular Beam Epitaxy of CdHgTe: Current State and Horizons. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2020, 56, 456-469.	0.6	5
48	Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. <i>JETP Letters</i> , 2019, 109, 657-662.	1.4	10
49	Suppressed Auger scattering and tunable light emission of Landau-quantized massless Kane electrons. <i>Nature Photonics</i> , 2019, 13, 783-787.	31.4	23
50	Topological Protection Brought to Light by the Time-Reversal Symmetry Breaking. <i>Physical Review Letters</i> , 2019, 123, 056801.	7.8	25
51	An Optical Study of Disorder in Cadmium Mercury Telluride Solid Solutions. <i>Technical Physics Letters</i> , 2019, 45, 553-556.	0.7	2
52	Magneto-transport in inverted HgTe quantum wells. <i>Npj Quantum Materials</i> , 2019, 4, .	5.2	16
53	On the Thermal Activation of Conductivity Electrons in a p-Type HgTe/CdHgTe Double Quantum Well with HgTe Layers of Critical Width. <i>Semiconductors</i> , 2019, 53, 919-922.	0.5	3
54	Residual-Photoconductivity Spectra in HgTe/CdHgTe Quantum-Well Heterostructures. <i>Semiconductors</i> , 2019, 53, 1363-1366.	0.5	4

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55	Photodetectors with 384 Å— 288 Matrix Elements for the Infrared Range of 8â€“10 Microns. Journal of Communications Technology and Electronics, 2019, 64, 1024-1029.	0.5	6
56	PT-Symmetric Terahertz Photoconductivity in Hg <sub>1-x</sub> Cd <sub>x</sub> Te. , 2019, , .		0
57	Far and Mid IR Stimulated Emission in HgCdTe QW Heterostructures. , 2019, , .		1
58	Second-Harmonic Generation of Subterahertz Gyrotron Radiation by Frequency Doubling in InP:Fe and Its Application for Magnetospectroscopy of Semiconductor Structures. Semiconductors, 2019, 53, 1217-1221.	0.5	6
59	Evolution of the Impurity Photoconductivity in CdHgTe Epitaxial Films with Temperature. Semiconductors, 2019, 53, 1266-1271.	0.5	2
60	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd <sub>0.7</sub> Hg <sub>0.3</sub> Te QWs Near 14 Î¼m. Semiconductors, 2019, 53, 1154-1157.	0.5	4
61	Determining the Compositional Profile of HgTe/CdxHg <sub>1-Âˆ</sub> Te Quantum Wells by Single-Wavelength Ellipsometry. Optics and Spectroscopy (English Translation of Optika I Spektroskopiya), 2019, 127, 340-346.	0.6	17
62	A Megapixel Matrix Photodetector of the Middle Infrared Range. Journal of Communications Technology and Electronics, 2019, 64, 1011-1015.	0.5	5
63	Spin splitting of surface states in HgTe quantum wells. Low Temperature Physics, 2019, 45, 159-164.	0.6	3
64	Topological surface states in thick partially relaxed HgTe films. Physical Review B, 2019, 99, .	3.2	11
65	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. JETP Letters, 2019, 109, 191-197.	1.4	2
66	High-frequency impact ionization and nonlinearity of photocurrent induced by intense terahertz radiation in HgTe-based quantum well structures. Physical Review B, 2019, 99, .	3.2	6
67	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. Condensed Matter, 2019, 4, 27.	1.8	5
68	Features of Magneto-Intersubband Oscillations in HgTe Quantum Wells. JETP Letters, 2019, 110, 301-305.	1.4	7
69	Shubnikovâ€”de Haas Oscillations in a Three-Dimensional Topological Insulator Based on a Strained HgTe Film in an Inclined Magnetic Field. JETP Letters, 2019, 109, 799-805.	1.4	2
70	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. Journal of Physics Condensed Matter, 2019, 31, 145501.	1.8	13
71	Express Characterization of Crystalline Perfection of CdxHg <sub>1-Âˆ</sub> Te Structures by Reflection Second Harmonic Generation of Probing Radiation. Optoelectronics, Instrumentation and Data Processing, 2019, 55, 447-454.	0.6	3
72	Temperature-Induced Topological Phase Transition in HgTe Quantum Wells. Physical Review Letters, 2018, 120, 086401.	7.8	43

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73	Probing spin helical surface states in topological HgTe nanowires. <i>Physical Review B</i> , 2018, 97, .	3.2	48
74	Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. <i>Journal of Experimental and Theoretical Physics</i> , 2018, 127, 1125-1129.	0.9	6
75	Advanced Design of Scanning Infrared Focal Plane Arrays. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2018, 54, 569-575.	0.6	2
76	Terahertz Cyclotron Photoconductivity in a Highly Unbalanced Two-Dimensional Electron-Hole System. <i>JETP Letters</i> , 2018, 108, 247-252.	1.4	6
77	Bipolar Persistent Photoconductivity in HgTe/CdHgTe (013) Double Quantum-Well Heterostructures. <i>Semiconductors</i> , 2018, 52, 1586-1589.	0.5	9
78	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. <i>JETP Letters</i> , 2018, 108, 329-334.	1.4	4
79	HgCdTe based quantum well heterostructures for long-wavelength lasers operating in 5 - 15 THz range. <i>Journal of Physics: Conference Series</i> , 2018, 1092, 012126.	0.4	0
80	Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. <i>Sensors</i> , 2018, 18, 4341.	3.8	4
81	Two-dimensional semimetal in HgTe quantum well under hydrostatic pressure. <i>Physical Review B</i> , 2018, 98, .	3.2	2
82	Magneto-optics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. <i>Semiconductors</i> , 2018, 52, 1386-1391.	0.5	4
83	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 495301.	1.8	22
84	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. <i>Semiconductors</i> , 2018, 52, 1375-1379.	0.5	6
85	Non-equilibrium electron transport induced by terahertz radiation in the topological and trivial phases of Hg <sub>1-x</sub> Cd <sub>x</sub> Te. <i>Beilstein Journal of Nanotechnology</i> , 2018, 9, 1035-1039.	2.8	25
86	Stimulated emission in the 28-35 $\mu$ m wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. <i>Optics Express</i> , 2018, 26, 12755.	3.4	26
87	Electron Effective Mass and g Factor in Wide HgTe Quantum Wells. <i>Semiconductors</i> , 2018, 52, 12-18.	0.5	4
88	Magneto-optical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. <i>Semiconductors</i> , 2018, 52, 436-441.	0.5	0
89	Transmission Spectra of HgTe-Based Quantum Wells and Films in the Far-Infrared Range. <i>Physics of the Solid State</i> , 2018, 60, 778-782.	0.6	1
90	Electrical Properties of the V-Defects of Epitaxial HgCdTe. <i>Journal of Electronic Materials</i> , 2017, 46, 4435-4438.	2.2	0

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91	Activation transport under quantum Hall regime in HgTe-based heterostructure. <i>Low Temperature Physics</i> , 2017, 43, 485-490.	0.6	3
92	HgCdTe-based heterostructures for terahertz photonics. <i>APL Materials</i> , 2017, 5, .	5.1	49
93	Robust helical edge transport at $\nu = 1/2$ quantum Hall state. <i>Physical Review B</i> , 2017, 96, .		
94	Valence band energy spectrum of HgTe quantum wells with an inverted band structure. <i>Physical Review B</i> , 2017, 96, .	3.2	30
95	Photogalvanic probing of helical edge channels in two-dimensional HgTe topological insulators. <i>Physical Review B</i> , 2017, 95, .	3.2	61
96	Ballistic geometric resistance resonances in a single surface of a topological insulator. <i>Nature Communications</i> , 2017, 8, 2023.	12.8	23
97	Activation conductivity in HgTe/CdHgTe quantum wells at integer Landau level filling factors: Role of the random potential. <i>Semiconductors</i> , 2017, 51, 1562-1570.	0.5	0
98	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. <i>Semiconductors</i> , 2017, 51, 1531-1536.	0.5	8
99	Terahertz Photoconductivity in $\text{Hg}_{1-x}\text{Cd}_x\text{Te}$ near the transition from the direct to inverted spectrum. <i>JETP Letters</i> , 2017, 106, 162-166.	1.4	16
100	Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to $19.5\ \mu\text{m}$ . <i>Applied Physics Letters</i> , 2017, 111, .	3.3	58
101	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. <i>Physical Review B</i> , 2017, 96, .	3.2	38
102	Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. <i>Semiconductor Science and Technology</i> , 2017, 32, 095007.	2.0	27
103	Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. <i>Semiconductors</i> , 2017, 51, 1557-1561.	0.5	6
104	Polarization Pyrometry of Layered Semiconductor Structures under Conditions of Low-Temperature Technological Processes. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2017, 53, 630-638.	0.6	2
105	Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 534-537.	0.8	2
106	CdHgTe heterostructures for new-generation IR photodetectors operating at elevated temperatures. <i>Semiconductors</i> , 2016, 50, 1626-1629.	0.5	4
107	Capacitance spectroscopy of a system of gapless Dirac fermions in a HgTe quantum well. <i>JETP Letters</i> , 2016, 104, 859-863.	1.4	12
108	Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. <i>Semiconductors</i> , 2016, 50, 1651-1656.	0.5	7

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109	Two-color arrays for sub-terahertz/infrared imaging. , 2016, , .		0
110	Long wavelength stimulated emission up to 9.5 $\mu\text{m}$ from HgCdTe quantum well heterostructures. Applied Physics Letters, 2016, 108, .	3.3	34
111	Weak antilocalization in a three-dimensional topological insulator based on a high-mobility HgTe film. JETP Letters, 2016, 104, 302-308.	1.4	6
112	Mercury vacancies as divalent acceptors in Hg <sub>y</sub> Te <sub>1-y</sub> /Cd <sub>x</sub> Hg <sub>1-x</sub> Te structures with quantum wells. Semiconductors, 2016, 50, 1662-1668.	0.5	6
113	HgTe/CdHgTe double quantum well with a spectrum of bilayer graphene and peculiarities of its magnetotransport. JETP Letters, 2016, 104, 403-410.	1.4	11
114	Investigation of the surface-potential distribution of epitaxial CdHgTe films. Journal of Surface Investigation, 2016, 10, 1096-1100.	0.5	1
115	The noise model of CTIA-based pixel of SWIR HgCdTe focal plane arrays. , 2016, , .		2
116	Magnetotransport in double quantum well with inverted energy spectrum: HgTe/CdHgTe. Physical Review B, 2016, 93, .	3.2	16
117	Spin-orbit splitting of valence and conduction bands in HgTe quantum wells near the Dirac point. Physical Review B, 2016, 93, .	3.2	38
118	Probing Quantum Capacitance in a 3D Topological Insulator. Physical Review Letters, 2016, 116, 166802.	7.8	43
119	Methodological and instrumental problems in high-precision in situ ellipsometry diagnostics of the mercury cadmium telluride layer composition in molecular beam epitaxy. Instruments and Experimental Techniques, 2016, 59, 857-864.	0.5	5
120	Magneto spectroscopy of double HgTe/CdHgTe quantum wells. Semiconductors, 2016, 50, 1532-1538.	0.5	9
121	Temperature-driven massless Kane fermions in HgCdTe crystals. Nature Communications, 2016, 7, 12576.	12.8	73
122	Zeeman splitting of the conduction band of HgTe quantum wells with a semimetallic spectrum. JETP Letters, 2016, 104, 241-247.	1.4	4
123	Cell of the silicon integrated reading circuit with built-it analog-digital converter. Optoelectronics, Instrumentation and Data Processing, 2016, 52, 381-387.	0.6	0
124	Defects in mercury-cadmium telluride heteroepitaxial structures grown by molecular-beam epitaxy on silicon substrates. Semiconductors, 2016, 50, 208-211.	0.5	5
125	Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. Semiconductors, 2015, 49, 1627-1633.	0.5	6
126	Shot noise of the edge transport in the inverted band HgTe quantum wells. JETP Letters, 2015, 101, 708-713.	1.4	29



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127	Evidence on the macroscopic length scale spin coherence for the edge currents in a narrow HgTe quantum well. JETP Letters, 2015, 101, 814-819.	1.4	18
128	Cyclotron-resonance-assisted photocurrents in surface states of a three-dimensional topological insulator based on a strained high-mobility HgTe film. Physical Review B, 2015, 92, .	3.2	74
129	Analysis of charge-carrier diffusion in the photosensing films of HgCdTe infrared focal plane array photodetectors. Journal of Applied Physics, 2015, 118, .	2.5	9
130	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. Applied Physics Letters, 2015, 107, .	3.3	13
131	Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. Journal of Physics: Conference Series, 2015, 647, 012008.	0.4	6
132	Temperature scaling in the quantum-Hall-effect regime in a HgTe quantum well with an inverted energy spectrum. Semiconductors, 2015, 49, 1545-1549.	0.5	11
133	Investigation of magnetoabsorption at different temperatures in HgTe/CdHgTe quantum-well heterostructures in pulsed magnetic fields. Semiconductors, 2015, 49, 1611-1615.	0.5	5
134	Quantum hall effect in a system of gapless Dirac fermions in HgTe quantum wells. JETP Letters, 2015, 100, 724-730.	1.4	16
135	Three-dimensional topological insulator based on a strained HgTe film. Low Temperature Physics, 2015, 41, 82-89.	0.6	4
136	Surface states in a HgTe quantum well and scattering by surface roughness. JETP Letters, 2015, 101, 330-333.	1.4	7
137	Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. JETP Letters, 2015, 100, 790-794.	1.4	26
138	Energy spectrum and transport in narrow HgTe quantum wells. Semiconductors, 2015, 49, 39-43.	0.5	2
139	Acceptor states in heteroepitaxial CdHgTe films grown by molecular-beam epitaxy. Semiconductors, 2015, 49, 367-372.	0.5	10
140	Persistence of a Two-Dimensional Topological Insulator State in Wide HgTe Quantum Wells. Physical Review Letters, 2015, 114, 126802.	7.8	63
141	Conductance of a lateral p-n junction in two-dimensional HgTe structures with an inverted spectrum: The role of edge states. JETP Letters, 2015, 101, 469-473.	1.4	3
142	Determination of charge-carrier diffusion length in the photosensing layer of HgCdTe n-on-p photovoltaic infrared focal plane array detectors. Applied Physics Letters, 2014, 104, 092112.	3.3	10
143	Metal-insulator transition in a HgTe quantum well under hydrostatic pressure. JETP Letters, 2014, 98, 843-847.	1.4	16
144	Photoluminescence of CdHgTe solid solutions subjected to low-energy ion treatment. Semiconductors, 2014, 48, 195-198.	0.5	5

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145	Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. <i>Nature Physics</i> , 2014, 10, 233-238.	16.7	190
146	Efficient long wavelength interband photoluminescence from HgCdTe epitaxial films at wavelengths up to 26 $\mu\text{m}$ . <i>Applied Physics Letters</i> , 2014, 104, .	3.3	35
147	Time resolved photoluminescence spectroscopy of narrow gap Hg <sub>1-x</sub> Cd <sub>x</sub> Te/Cd <sub>y</sub> Hg <sub>1-y</sub> Te quantum well heterostructures. <i>Applied Physics Letters</i> , 2014, 105, 022102.	3.3	28
148	Hole transport and valence-band dispersion law in a HgTe quantum well with a normal energy spectrum. <i>Physical Review B</i> , 2014, 89, .	3.2	17
149	Transport Properties of a 3D Topological Insulator based on a Strained High-Mobility HgTe Film. <i>Physical Review Letters</i> , 2014, 112, 196801.	7.8	73
150	Temperature dependence of the resistance of a two-dimensional topological insulator in a HgTe quantum well. <i>Physical Review B</i> , 2014, 89, .	3.2	63
151	Terahertz electron transport in a two-dimensional topological insulator in a HgTe quantum well. <i>JETP Letters</i> , 2014, 99, 290-294.	1.4	7
152	Sub-terahertz photoconductivity of Hg <sub>x</sub> Cd <sub>1-x</sub> Te crystals with composition close to semiconductor-to-semimetal topological transition. , 2014, , .		0
153	Giant photocurrents in a Dirac fermion system at cyclotron resonance. <i>Physical Review B</i> , 2013, 87, .	3.2	65
154	Increasing the mechanical strength of hybrid photodetectors based on mercury-cadmium-telluride heteroepitaxial layers. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2013, 49, 94-100.	0.6	2
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